



Sheet 1 of 1

Form 1449*

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INFORMATION DISCLOSURE STATEMENT
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Applicant: Zhongze Wang et al.

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U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>Se</i>	5,739,066	04/14/1998	Pan, P.	438	595	09/17/96

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner Initial	
<i>Se</i>	Ghani, T., et al., "100 nm Gate Length High Performance / Low Power CMOS Transistor Structure", <u>IEEE</u> , 4 pages, (1999)

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*Substitute Disclosure Statement Form (PTO-1449)

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